

Innovative Photon Management for Smart Control of Light

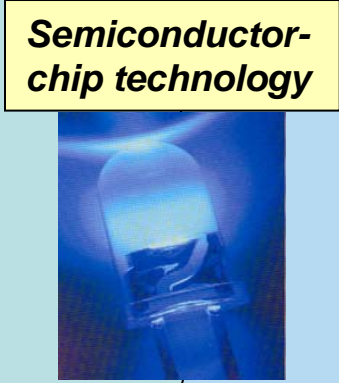
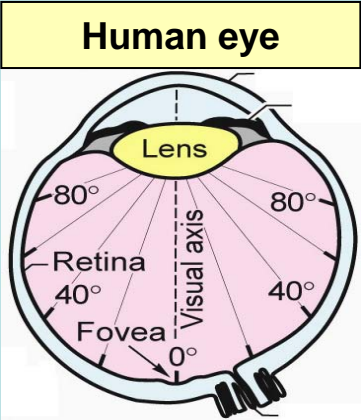
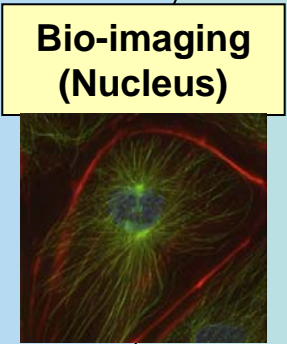
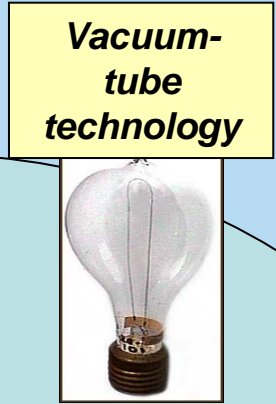
Shawn-Yu Lin

Device Thrust Leader

RPI Constellation Professor (The Future-Chips)

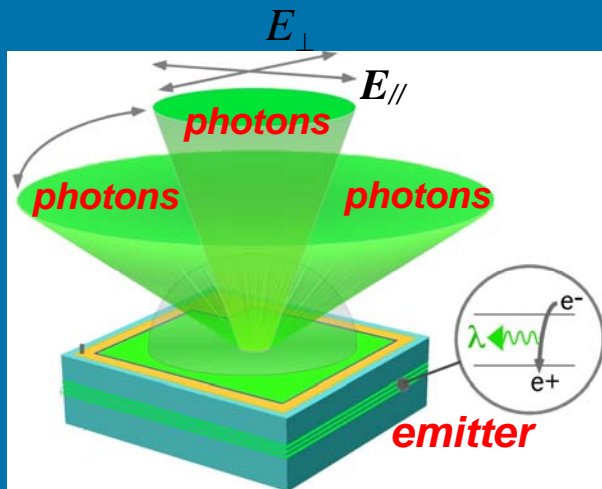


Light, Visual Experience & Innovation

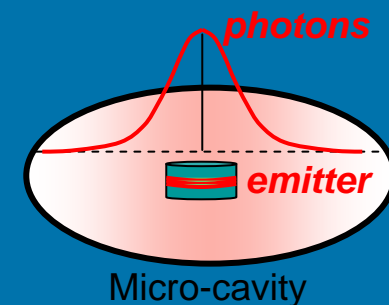
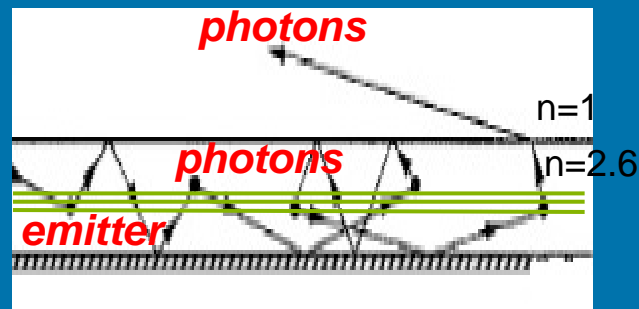


(Summer Davos 09, photonic revolution, opening remark-1/2, Dr. SY Lin-RPI, USA)

What are the most innovative contributions? the New Science of LED - tailoring the emitter-photon interaction -



$C_{ex} > 80-100\%^{**}$



$\eta_{int} > 90\%^{***}$

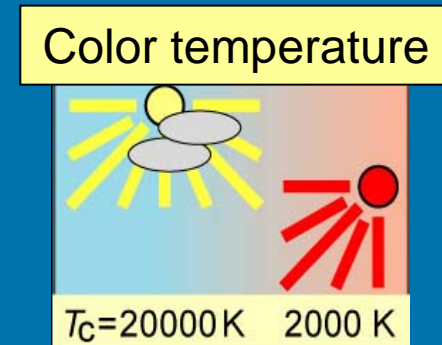
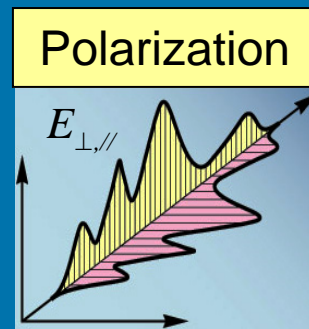
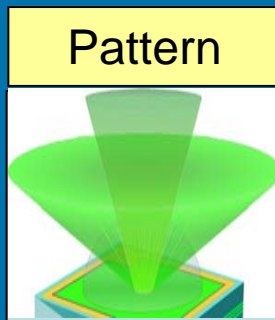
- **Guided modes** –eliminate
- Rad. pattern- ($\Delta\theta < 10^\circ$)

- **Guided/ trapped light** (4%)
- Rad. pattern- Lambertian
- Un-polarized- $\theta \sim 0^\circ$

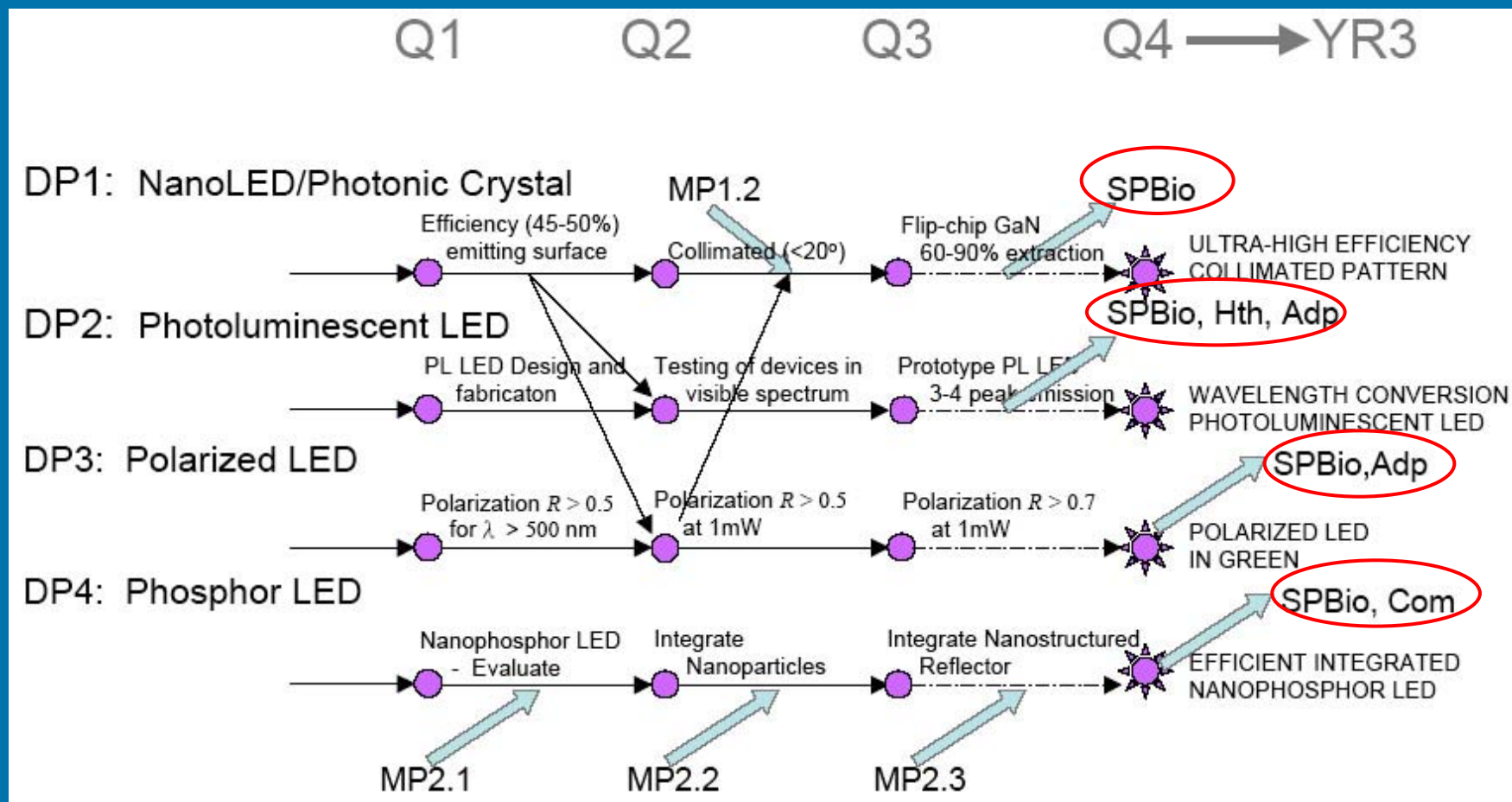
- **Cavity modes**
- Emitter-photon- coupled

(**source: Laser & Photonics Rev. 1, 307-333, 2007, ***Nature 425, 268, 2003)

On-Chip Control of the Nature of Light



Under This ERC, We Have Identified 4 Areas as our Device Focus for Year 2-3.



(from Art Sanderson Nov. 09)

DP: Device Project
 SP: System Project

We Have Formulated a Preliminary List of Device Performance Matrix As our Near-Term Objectives.

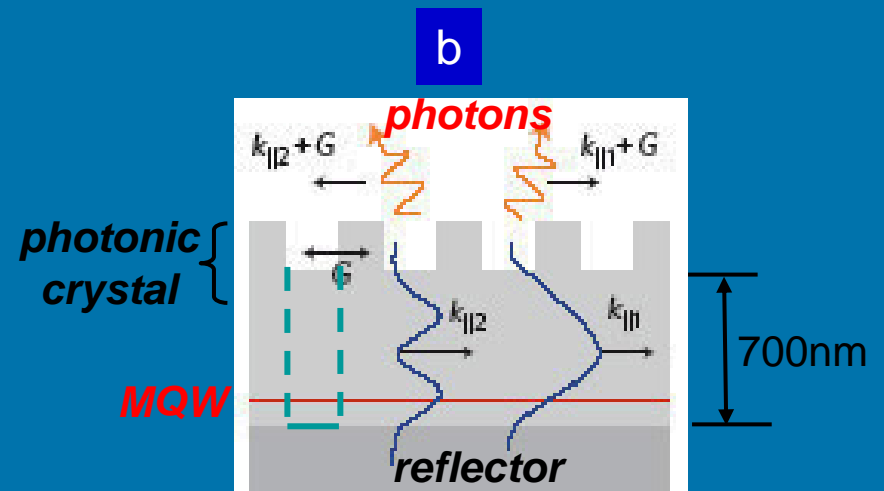
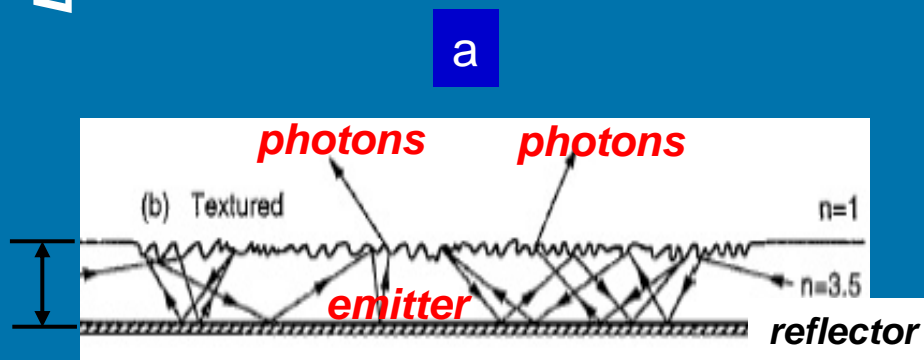
- 1. Wavelength bandwidth (variable/tunable/ $\Delta\lambda$ 30/10nm)
- 2. Brightness (C_{ex} , η , droop effect)
3. Uniformity (0.25mm², 5mm², 50mm²)
- 4. Directionality /emission θ (30/20/10⁰)
- 5. Polarization selectivity (2:1/10:1/50:1)
6. Phosphor lifetime (100ns/10ns/1nsec)
new device design **Broadband green**
Narrowband red
7. Color mixing (spectral uniformity)
8. Thermal management
- 9. Fabrication technology (70nm over 625mm²)

What are the trade-offs in optimizing for system performance?

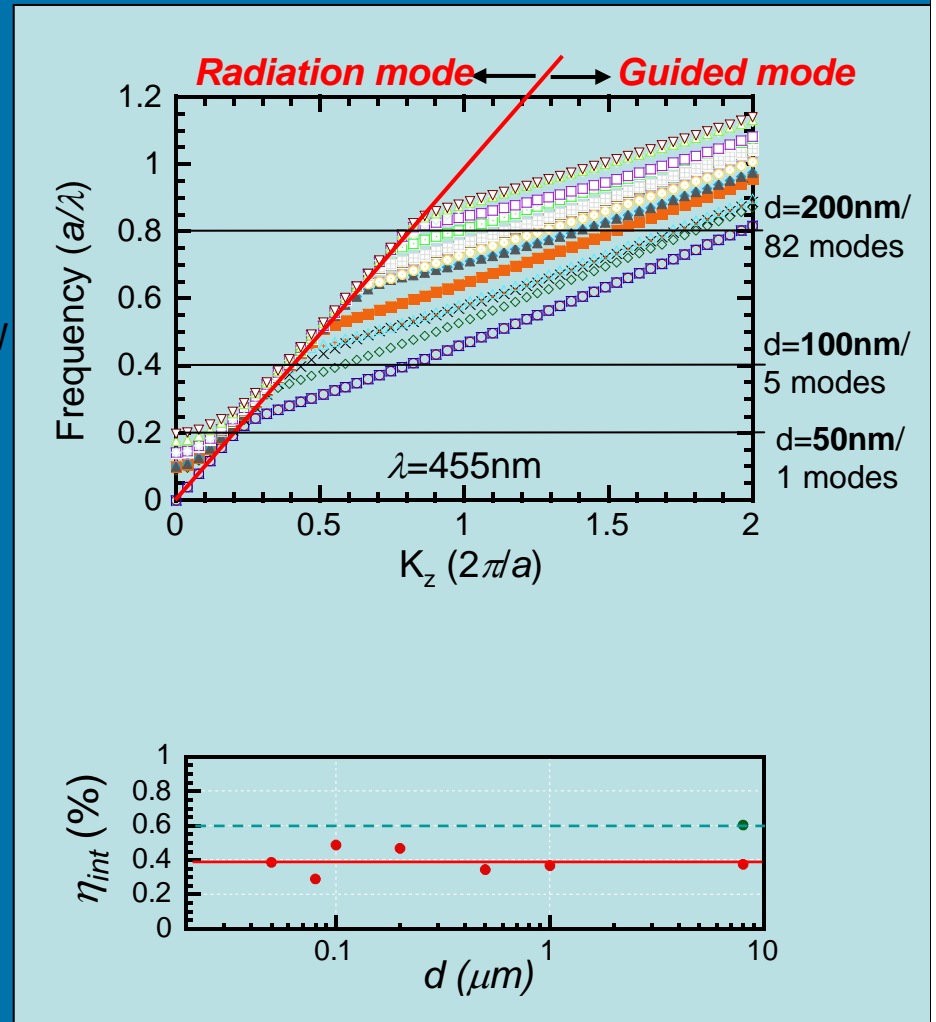
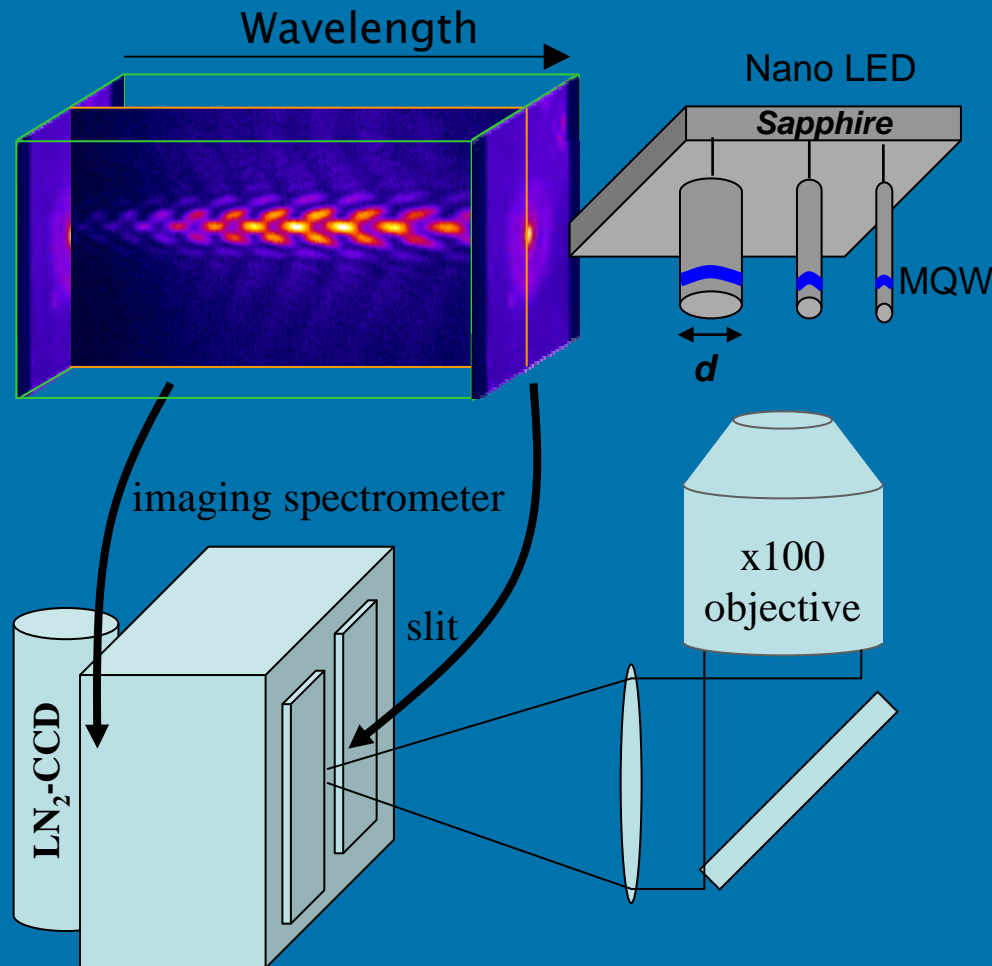
The key performance attributes and characteristics- (I) extraction and radiation pattern

Device Grand Challenge

Approach	Principle	C (extraction)	Source
a. Surface texture +thin film-reflector	Optical scattering; FP cavity	External efficiency: 46%	APL 63, 2174, '93 APL 79, 2315, '01
b. Photonic crystal +thin film-reflector	Bloch scattering; FP cavity	68-78% (total) - 1mA	Nature Photonics 3, 163, 2009
c. Nano LED***	Single-mode or few modes	50-70% (one-side)	
d. Nano LED*** +thin film-reflector	Single-mode; FP cavity	Expect: >80-90% (total)	

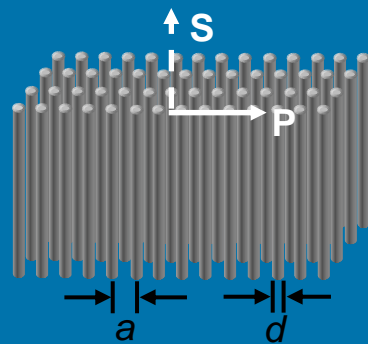
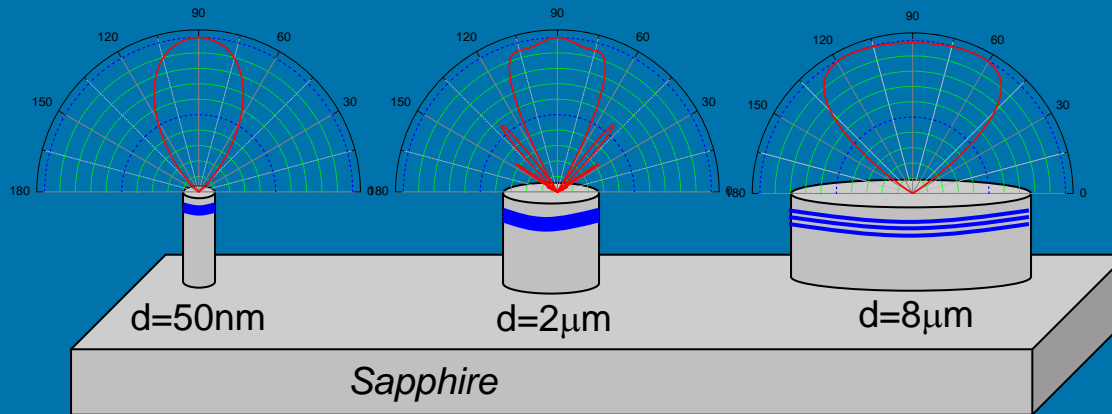


Engineering the Basic Optical Mode : LED Light Extraction and Pattern Control

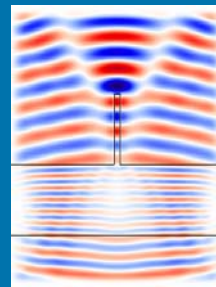


(data to be published)

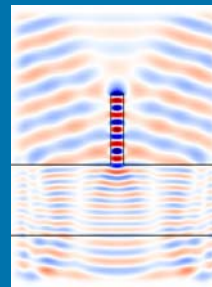
Nano Engineering of the Basic Mode Also Allows Us to Tailor an LED's Radiation Pattern.



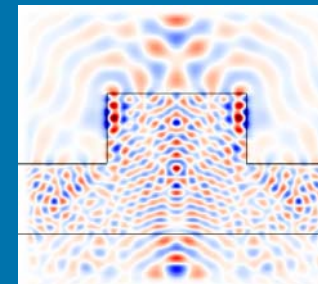
Next: 2D Array



$d=100\text{nm}$

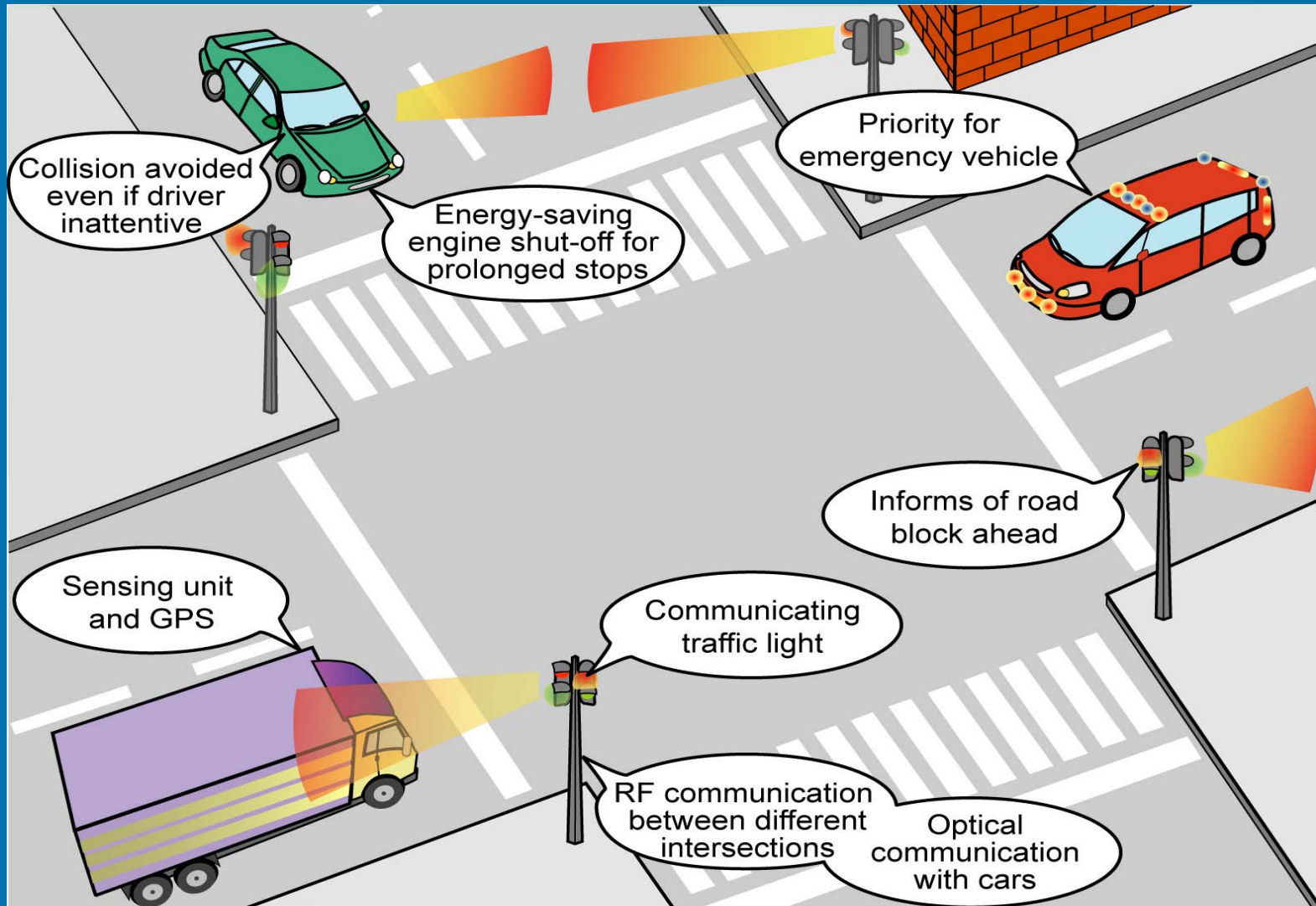


$d=200\text{nm}$



$d=2,000\text{nm}$

“Beam Shaping” for Lighting and Communication

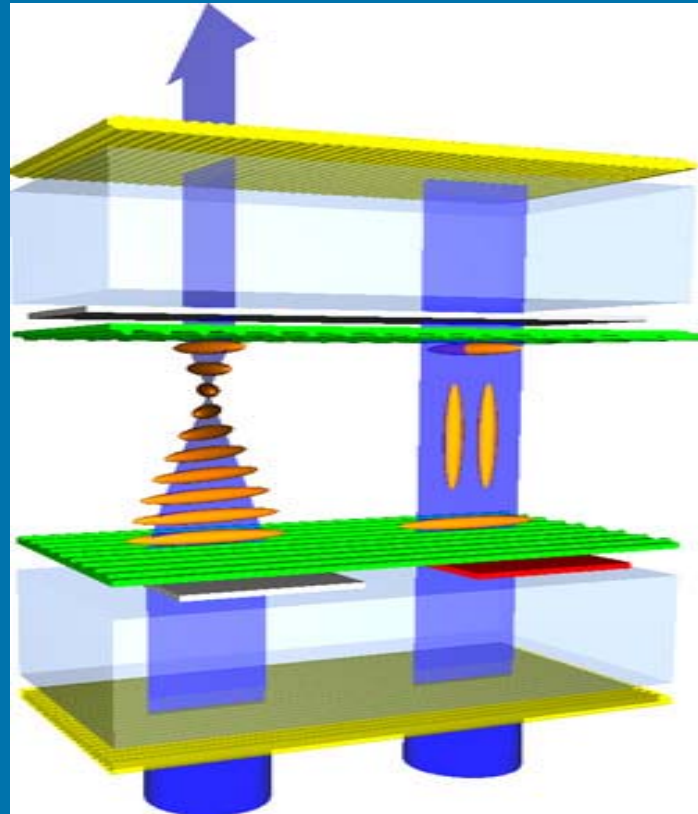


“Polarized LED” for Display Application

Polarizer

**Liquid
crystal**

Polarizer



CCFL



High-power LED

**Backlighting/
Edge injection/
Waveguiding**

“Smart” features :

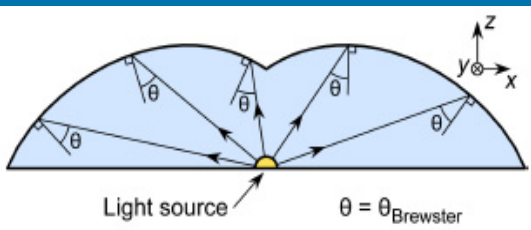
- Reduced motion blur by impulse driving
- Color filter-less LCD by sequential driving

The key performance attributes, characteristics- (II) polarization.

LED Device Grand Challenge

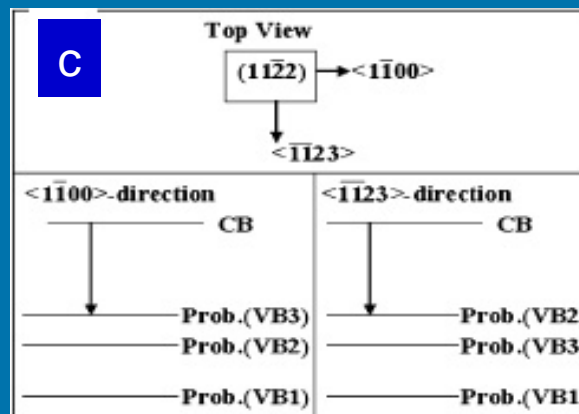
Approach	Principle	Polar. ratio	Comments	Source
a. External Reflector	Critical angle	2:1	Bulky; Emis. angle dependent	Op. Express 15, 11213, '09
b. Metallic grating	Metallic loss	2:1		APL 93, 23111, '08
c. strain engineering**	VB degeneracy	2:1 (522nm) 5:1 (588nm)	Growth intensive; High In-concentration;	JJAP 47, 7854, 2008
d. Metallic/ plasmonic photonic crystal**	Plasmonic coupling	10:1 (expect)	Metal loss at visible Light focusing at corners	

a

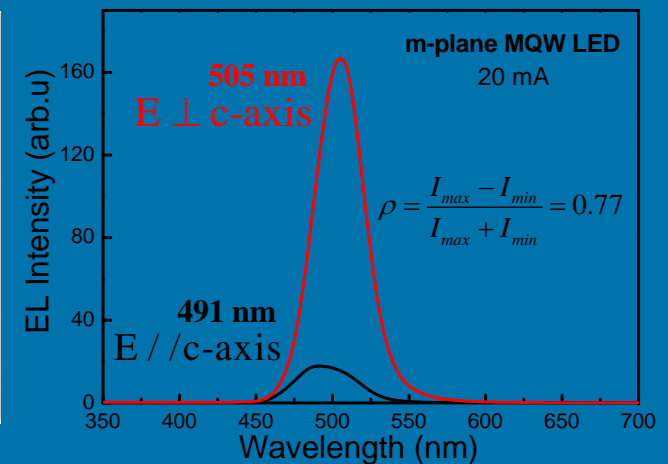


External reflector

c

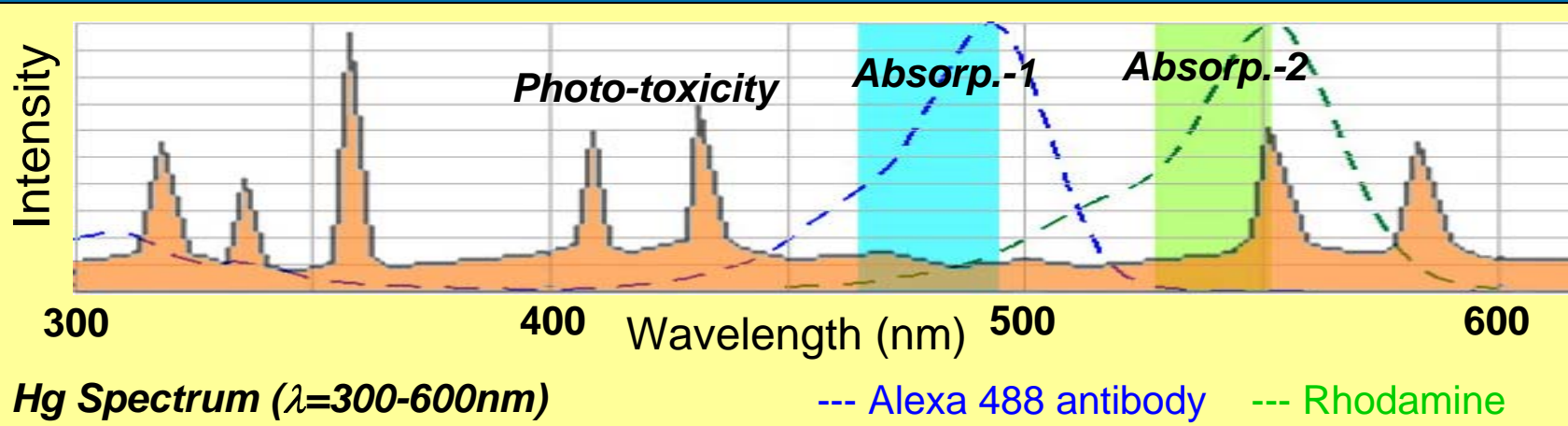


VB Strain Engineering



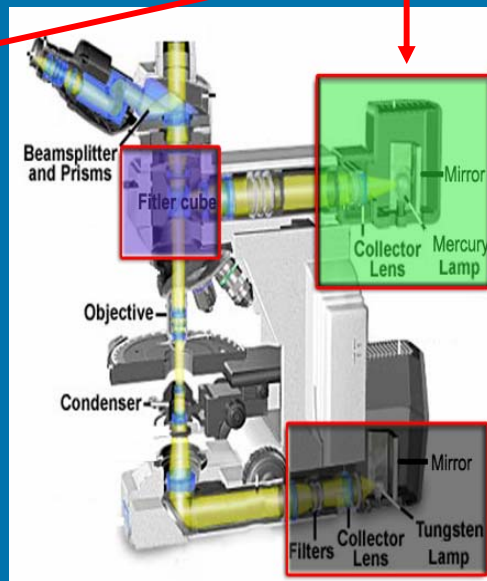
(from C. Wetzel et al.)

For Bio-Imaging Applications, There is a Need for Wavelength and Intensity Control.



LED Advantages:

- λ -selective
- Photo-toxicity
- Compact, low cost
- Full spectral
- Polarization



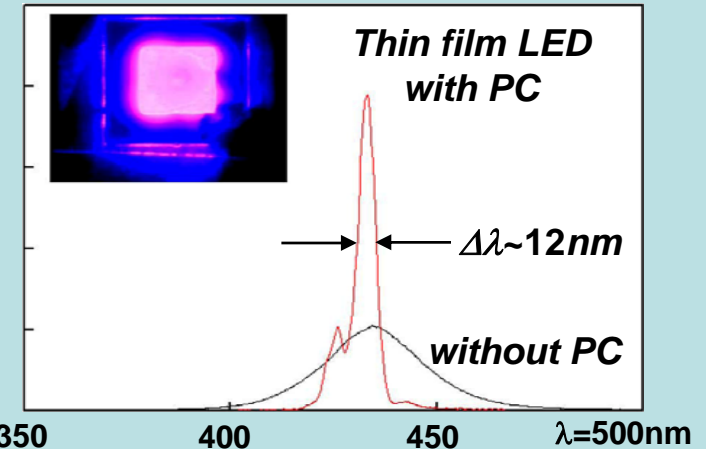
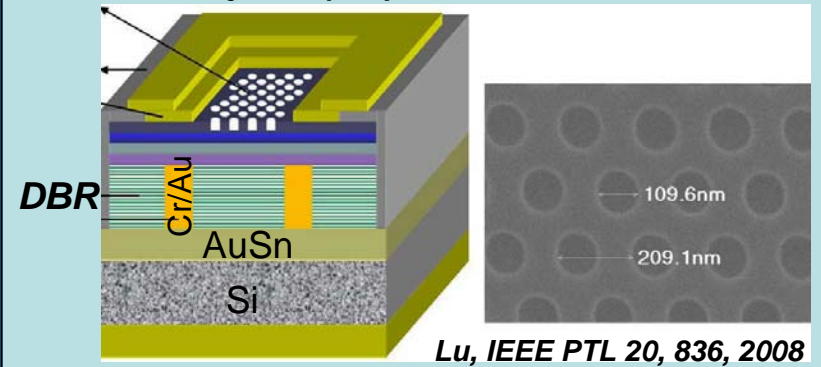
Approach for Bandwidth-Control and Wavelength-Tuning.

LED Device Grand Challenges (Bio-imaging)

Match LED- λ to fluorophore
 $\Delta\lambda=30\text{nm}$ (desired), $\Delta\lambda=10\text{nm}$ (ideal)

- Dynamic λ -tuning
- Polarized LED
- Collimated emission

Photonic crystal (PC)



Novel features:

- Engineering of op. modes
 - Global resonance, not μ -cavity
 - High Intensity
 - Narrow $\Delta\lambda$
- Next: DBR, tunable

Abso. Emission

	Abso.	Emission	
Y66W	436	485	
mKeima-Red	440	620	monomer (MBL)
TagCFP	458	480	dimer (Evrogen)
AmCyan1	458	489	tetramer, (Clontech)
mTFP1	462	492	dimer
S65A	471	504	
Midoriishi Cyan	472	495	dimer (MBL)
Wild Type GFP	396,475	508	
S65C	479	507	
TurboGFP	482	502	dimer, (Evrogen)
TagGFP	482	505	monomer (Evrogen)
S65L	484	510	
Emerald	487	509	weak dimer, (Invitrogen)

Phosphor Device: Bulk Crystal

Growth of Multi-component, Rare Earth Doped Thio-gallate

- Growth of $(\text{Sr}_{1-x}\text{Ca}_x\text{Ga}_y\text{In}_{1-y}\text{S}:\text{Eu})$ from high temperature melt:
- Material selected for comparison with industry results on phosphor LEDs
- Fabricated preliminary *down-conversion* structures
(excitation @ 451 nm blue LED)
(emission area in photos : 3cm^2)



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Low temperature growth of $\text{Ga}_{1-x}\text{In}_x\text{P}$ bulk crystals from InSb-rich melt

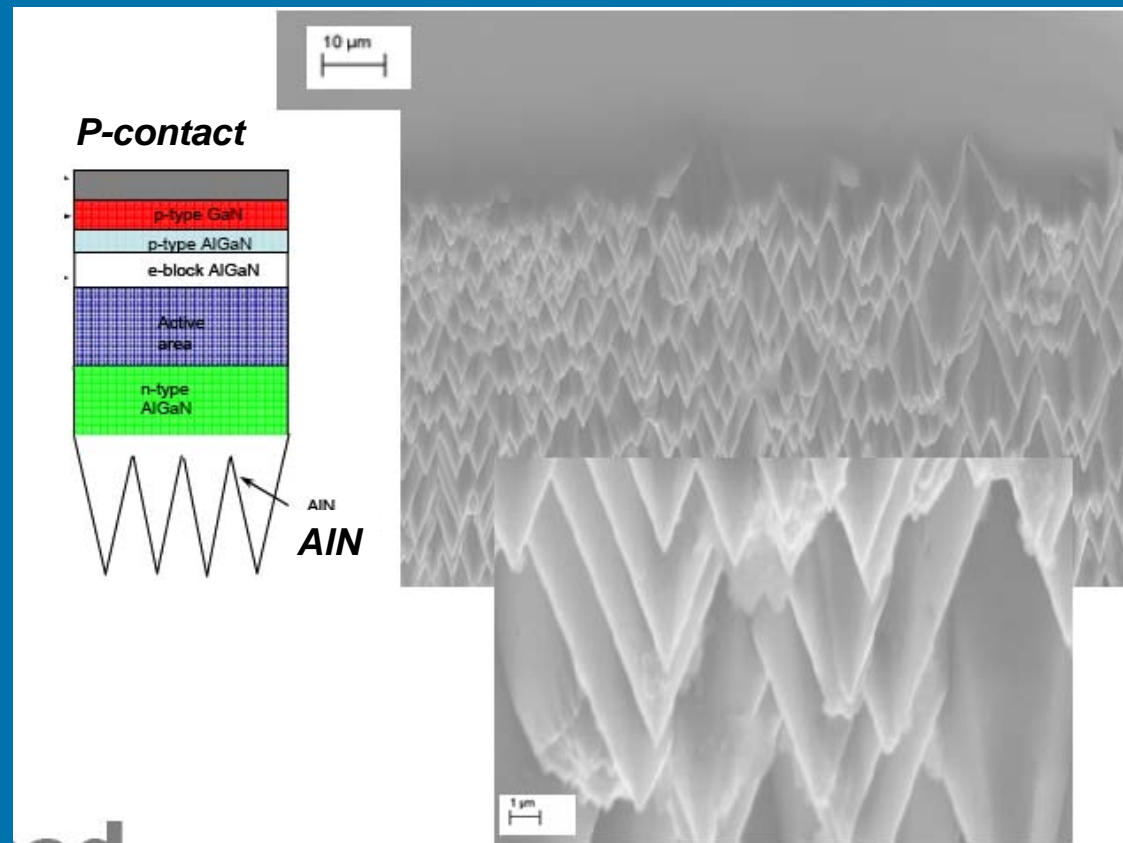
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^b Department of Electrical, Computer, and Systems Engineering, Rensselaer Polytechnic Institute, Troy, NY 12180, USA

We Have On-going and Active Industrial Collaborations With Our Industrial Partners.

“The biggest problem we face in UV-LED is extraction. We loss 95% of light due to a poor extraction.” - Leo Schowalter of Crystal IS



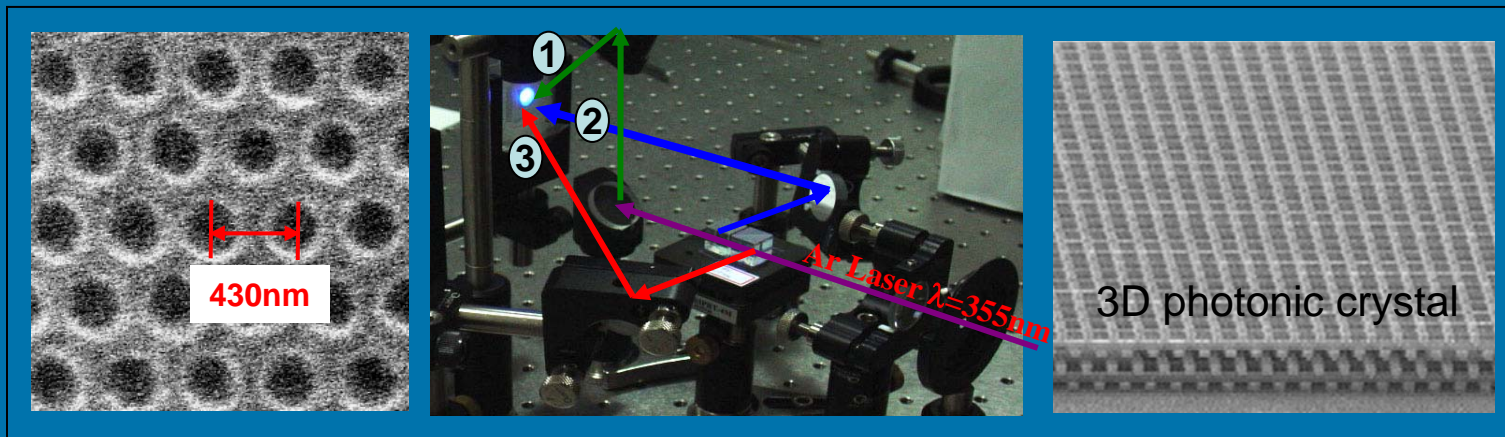
(from Crystal IS)

UV-LED Device Grand Challenge

: backside emission/ thick epi-layer/ front absorption

On Fabrication Technology - Large scale and Low cost

Approaches	Feature size	Size Scale	Pro. speed	Comments
e-beam write	<10nm	300 x 300 μm ₂	Slow	Expensive
Nano-imprint	50-150nm	5 x 5 cm ²	fast	Molding material
Interferometric lithography*** (Steve Brueck/ UNM)	50-150nm	5 x 5 cm ²	fast	Optics/ 2D pattern
Holographic lithography (RPI)	50-150nm	5 x 5 cm ²	fast	Optics/ 3D pattern



(SY Lin and Prof. M.L. Hsieh, NTNU, Taiwan)

Our team has world renowned expertise in nanofabrication.

Dr. S. Brueck, pioneers the interferometric lithography method.

Dr. S. Y. Lin pioneers the nanofabrication of 2D and 3D photonic crystals.

Thank you!